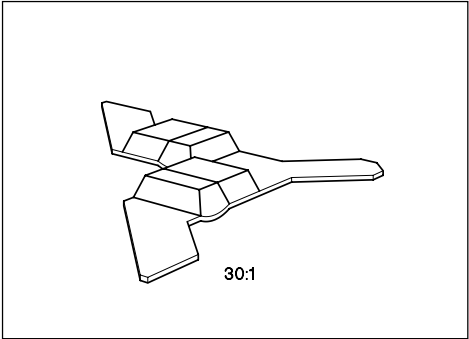


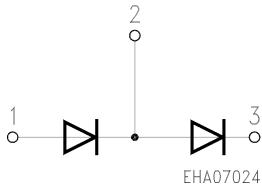
Silicon Schottky Diodes

BAT 15- ... D

- Beam lead technology
- Low dimension
- High performance
- Low barrier



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration	Package ¹⁾
BAT 15-020 D	—	Q62702-D1263		D
BAT 15-050 D		Q62702-D3450		
BAT 15-090 D		Q62702-D1280		
BAT 15-110 D		Q62702-D1289		

Maximum Ratings

Parameter	Symbol	Values		Unit
		BAT 15-020 D BAT 15-050 D	BAT 15-090 D BAT 15-110 D	
Reverse voltage	V_R	4	4	V
Forward current	I_F	100	50	mA
Junction temperature	T_j	175		°C
Storage temperature range	T_{stg}	− 65 ... + 150		
Operating temperature range	T_{op}	− 65 ... + 150		

¹⁾ For detailed information see chapter Package Outlines.

Electrical Characteristicsat $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Breakdown voltage $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)}$	4	—	—	V
Diode capacitance $V_R = 0, f = 1\text{ MHz}$	C_T				pF
BAT 15-020 D		—	0.30	0.35	
BAT 15-050 D		—	0.20	0.25	
BAT 15-090 D		—	0.14	0.15	
BAT 15-110 D		—	0.10	0.12	
Forward voltage $I_F = 1\text{ mA}$	V_F				V
BAT 15-020 D		—	0.26	—	
BAT 15-050 D		—	0.28	—	
BAT 15-090 D		—	0.30	—	
BAT 15-110 D		—	0.31	—	
$I_F = 10\text{ mA}$					
BAT 15-020 D		—	0.35	—	
BAT 15-050 D		—	0.39	—	
BAT 15-090 D		—	0.44	—	
BAT 15-110 D		—	0.45	—	
Single sideband noise figure $F_{IF} = 1.5\text{ dB}, P_{LO} = 0\text{ dBm}, f_{IF} = 10.7\text{ MHz}$	F_{SSB}				dB
$f = 3.0\text{ GHz}$		—	6.0	—	
$f = 6.0\text{ GHz}$		—	6.5	—	
$f = 9.3\text{ GHz}$		—	6.5	—	
$f = 16\text{ GHz}$		—	7.0	—	
Differential forward resistance $I_F = 10\text{ mA}$	r_f				Ω
BAT 15-020 D		—	3.5	—	
BAT 15-050 D		—	4.0	—	
$I_F = 50\text{ mA}$					
BAT 15-090 D		—	7.0	—	
BAT 15-110 D		—	10.0	—	